

VHF POWER MOSFET

N-Channel Enhancement Mode

DESCRIPTION:

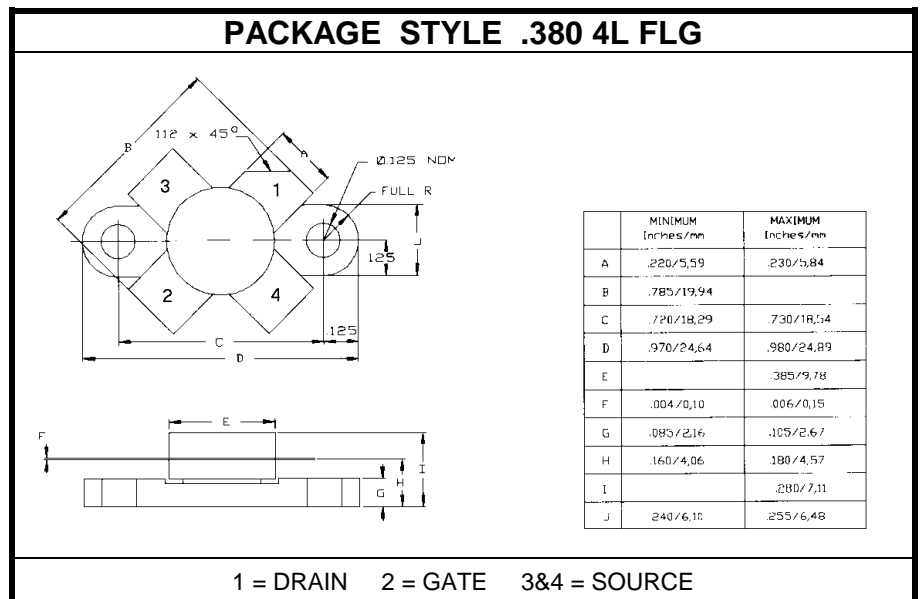
The **ASI BLF246** is a vertical D-MOS transistor designed for large signal amplifier applications in the VHF frequency range.

FEATURES INCLUDE:

- $P_G = 13$ dB Typical at 175 MHz
- 30:1 Load VSWR Capability
- *Omnigold™* metalization system

MAXIMUM RATINGS

I_D	13 A
V_{DS}	65 V
V_{GS}	± 20 V
P_{DISS}	130 W @ $T_C = 25$ °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.35 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_D = 50$ mA	65			V
I_{DSS}	$V_{DS} = 28$ V $V_{GS} = 0$ V			2.5	mA
I_{GSS}	$V_{DS} = 0$ V $V_{GS} = \pm 20$ V			1.0	μ A
$V_{GS(th)}$	$V_{DS} = 10$ V $I_D = 50$ mA	2.0		4.5	V
g_{fs}	$V_{DS} = 10$ V $I_D = 2.5$ A	3.0	4.2		S
$R_{DS(on)}$	$V_{GS} = 10$ V $I_D = 5.0$ A		0.2	0.3	Ω
C_{is} C_{os} C_{rs}	$V_{DS} = 28$ V $V_{GS} = 0$ V $f = 1.0$ MHz		225 180 25		pF
P_G η_D	$V_{DS} = 28$ V $P_{out} = 80$ W $f = 108$ MHz $I_{DQ} = 0.1$ A	16 55			dB %